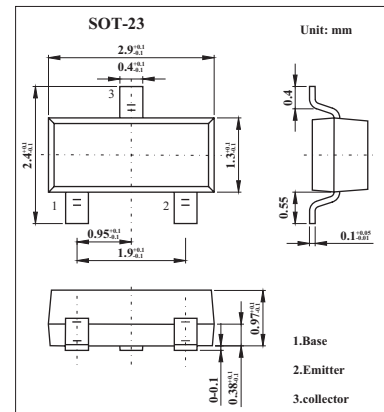


Silicon PNP Epitaxial

2SA1121

■ Features

- Low frequency amplifier

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CB0}	-35	V
Collector to emitter voltage	V_{CEO}	-35	V
Emitter to base voltage	V_{EBO}	-4	V
Collector current	I_C	-500	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\text{ mA}, I_E = 0$	-35			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{ mA}, R_{BE} = \infty$	-35			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\text{ mA}, I_C = 0$	-4			V
Collector cutoff current	I_{CBO}	$V_{CB} = -20\text{ V}, I_E = 0$			-0.5	μA
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -150\text{ mA}, I_B = -15\text{ mA}$		-0.2	-0.6	V
DC current transfer ratio	h_{FE}	$V_{CE} = -3\text{ V}, I_C = -10\text{ mA}$	60		320	
Base to emitter voltage	V_{BE}	$V_{CE} = -3\text{ V}, I_C = -10\text{ mA}$		-0.64		V

■ h_{FE} Classification

Marking	SB	SC	SD
h_{FE}	60~120	100~200	160~320